							Sheet 1 of	1 sheets
U.S. Department of Commerce, Patent and Trademark Office					Docket No. AMAT/6437/ETCH/METAL/JB1 Applicant Hwang, et al.		Serial No. 10/092,456 Confirmation No. 1212	
(PTO Form 1449 modified)								
INFORMATION DISCLOSURE STATEMENT BY APPLICANT								
(Use several sheets if necessary)					Filing Date		Group	
Examiner Dung Anh Le U.S. Patent Documents					March 6, 2002		2818	
U.S. Paten	t Docui	ments		VARIO				
*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date Appropriate	
	A1	\						
	A2							
	А3	\						
	A4	\						
	A5	λ						
Foreign Pa	tent Do	ocuments						
*Examiner		Document	Date	Country	Class	Subclass	Translation	
Initial		Number					YES	NO
	B1	V						
	B2	igg						
	В3							
	B4	\						
	B5							
OTHER AF	ET							
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.						
Jle	C1	Jung, K.B., et al., "Long term stability of dry etched magnetoresistive random access memory elements", <i>Journal of Vacuum Science and Technology:Part A</i> ; American Institute of Physics, New York, U.S., Vol. 18, No. 1, January 2000 (2000-01), pp. 268-272, XP001145970, ISSN: 0734-2101.						
He	C2	van Delft, F.C.M.J.M., et al., "The etch mechanisms of magnetic materials in an HCl plasma", Fusion Technology and Plasmas Session of the Twelth International Vacuum Congress (IVC-12) and Eighth International Conference on Solid Surfaces (ICSS-8), The Hague, Netherlands, 12-16 Oct. 1992, Vol. 200, No. 3, pp. 366-370, XP008022404, Journal of Nuclear Materials, May 1993, Netherlands, ISSN: 0022-3115.						
Sh	C3	Cho, H. et al., "Inductively coupled plasma etching of CoFeB, CoZr, CoSm and FeMn thin films in interhalogen mixtures", <i>Materials Science and Engineering B (Solid-State Materials for Advanced Technology)</i> , 15 June 1999, Elsevier, Switzerland, Vol. B60, No. 2, pp. 107-111, XP004175032, ISSN: 0921-5107.						
Examiner		Dl			Date Con	sidered Apr	11-20	64
*EXAMINER	t in conf	f reference considermance and not	dered, whether considered. In	or not citation is in c clude copy of this fo	conformance or with your	with MPEP 609; communication t	Draw line throo applicant.	ough